

Product Overview

NTMFS4H02NF: Single N-Channel Power MOSFET 25V, 193A, 1.4mΩ

For complete documentation, see the data sheet.

Power MOSFET 25 V, 193 A, Single N-Channel, SO-8FL

Features

- Integrated Schottky Diode
- Optimized Design to Minimize Conduction and Switching Losses
- Optimized Package to Minimize Parasitic Inductances
- Optimized material for improved thermal performance
- RoHS Compliant

Applications

- High Performance DC-DC Converters
- Point of Load
- System Voltage Rails

End Products

- Netcom, Telecom
- Server

Part Electrical Specifications

Product	Compliance	Status	Chan- nel Polar- ity	Confi- gura- tion	$V_{SS}^{(BR)D}$ Min (V)	V_{GS}^{max} (V)	$V_{GS}^{(th)}$ Max (V)	I_D Max (A)	P_D Max (W)	$R_{DS(on)}$ Max @ $V_{GS} =$ 2.5 V (mΩ)	$R_{DS(on)}$ Max @ $V_{GS} =$ 4.5 V (mΩ)	$R_{DS(on)}$ Max @ $V_{GS} =$ 10 V (mΩ)	Q_g Typ @ $V_{GS} =$ 4.5 V (nC)	Q_g Typ @ $V_{GS} =$ 10 V (nC)	C_{iss} Typ (pF)	Pack- age Type
NTMFS4H02NFT1G	Pb-free Halide free	Active	N- Chan- nel	Singl- e	25	20	2.1	193	83	-	2.3	1.4	26	18	2652	SO- 8FL / DFN- 5
NTMFS4H02NFT3G	Pb-free Halide free	Active	N- Chan- nel	Singl- e	25	20	2.1	193	83	-	2.3	1.4	26	18	2652	SO- 8FL / DFN- 5

For more information please contact your local sales support at www.onsemi.com.

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